

# [DUMMY PROCESS AND POLISHING-PAD CONDITIONING PROCESS FOR CHEMICAL MECHANICAL POLISHING APPARATUS]

## Abstract

A dummy process and a polishing-pad conditioning process suitable for a chemical mechanical polishing (CMP) is provided. The CMP apparatus includes a polishing head, a polishing table, and a polishing pad. The polishing head includes a protective hood, a base, a retaining ring and a wafer supporting assembly. The wafer is attached to an attaching surface in the wafer receiving recess. Next, the wafer supporting assembly is moved to make the bottom surface of the retaining ring more protrusive than the bottom surface of the wafer such that the wafer does not contact the surface of the polishing pad. Accordingly, the need for a large number of dummy wafers can be effectively avoided.